



# UNITED STATES PATENT AND TRADEMARK OFFICE

UNITED STATES DEPARTMENT OF COMMERCE  
United States Patent and Trademark Office  
Address: COMMISSIONER FOR PATENTS  
P.O. Box 1450  
Alexandria, Virginia 22313-1450  
www.uspto.gov

APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
10/731,089	12/10/2003	Shinya Sasagawa	740756-2676	6646
22204	7590	05/18/2006		
NIXON PEABODY, LLP 401 9TH STREET, NW SUITE 900 WASHINGTON, DC 20004-2128				
			EXAMINER ANGADI, MAKI A	
			ART UNIT 1765	PAPER NUMBER

DATE MAILED: 05/18/2006

Please find below and/or attached an Office communication concerning this application or proceeding.

<b>Office Action Summary</b>	<b>Application No.</b>	<b>Applicant(s)</b>	
	10/731,089	SASAGAWA ET AL.	
	<b>Examiner</b>	<b>Art Unit</b>	
	Maki A. Angadi	1765	

-- The MAILING DATE of this communication appears on the cover sheet with the correspondence address --

#### Period for Reply

A SHORTENED STATUTORY PERIOD FOR REPLY IS SET TO EXPIRE 3 MONTH(S) OR THIRTY (30) DAYS, WHICHEVER IS LONGER, FROM THE MAILING DATE OF THIS COMMUNICATION.

- Extensions of time may be available under the provisions of 37 CFR 1.136(a). In no event, however, may a reply be timely filed after SIX (6) MONTHS from the mailing date of this communication.
- If NO period for reply is specified above, the maximum statutory period will apply and will expire SIX (6) MONTHS from the mailing date of this communication.
- Failure to reply within the set or extended period for reply will, by statute, cause the application to become ABANDONED (35 U.S.C. § 133). Any reply received by the Office later than three months after the mailing date of this communication, even if timely filed, may reduce any earned patent term adjustment. See 37 CFR 1.704(b).

#### Status

- 1) ☐ Responsive to communication(s) filed on 10 December 2003.
- 2a) ☐ This action is **FINAL**. 2b) ☒ This action is non-final.
- 3) ☐ Since this application is in condition for allowance except for formal matters, prosecution as to the merits is closed in accordance with the practice under *Ex parte Quayle*, 1935 C.D. 11, 453 O.G. 213.

#### Disposition of Claims

- 4) ☒ Claim(s) 1-32 is/are pending in the application.
- 4a) Of the above claim(s) \_\_\_\_\_ is/are withdrawn from consideration.
- 5) ☐ Claim(s) \_\_\_\_\_ is/are allowed.
- 6) ☒ Claim(s) 1-32 is/are rejected.
- 7) ☐ Claim(s) \_\_\_\_\_ is/are objected to.
- 8) ☐ Claim(s) \_\_\_\_\_ are subject to restriction and/or election requirement.

#### Application Papers

- 9) ☐ The specification is objected to by the Examiner.
- 10) ☐ The drawing(s) filed on \_\_\_\_\_ is/are: a) ☐ accepted or b) ☐ objected to by the Examiner.  
Applicant may not request that any objection to the drawing(s) be held in abeyance. See 37 CFR 1.85(a).  
Replacement drawing sheet(s) including the correction is required if the drawing(s) is objected to. See 37 CFR 1.121(d).
- 11) ☐ The oath or declaration is objected to by the Examiner. Note the attached Office Action or form PTO-152.

#### Priority under 35 U.S.C. § 119

- 12) ☒ Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f).
- a) ☐ All b) ☐ Some \* c) ☐ None of:
1. ☐ Certified copies of the priority documents have been received.
  2. ☒ Certified copies of the priority documents have been received in Application No. JAPAN 2002-361924.
  3. ☐ Copies of the certified copies of the priority documents have been received in this National Stage application from the International Bureau (PCT Rule 17.2(a)).

\* See the attached detailed Office action for a list of the certified copies not received.

#### Attachment(s)

- |   |   |
|---|---|
| 1) <input checked="" type="checkbox"/> Notice of References Cited (PTO-892)   | 4) <input type="checkbox"/> Interview Summary (PTO-413)<br>Paper No(s)/Mail Date. _____ |
| 2) <input type="checkbox"/> Notice of Draftsperson's Patent Drawing Review (PTO-948)  | 5) <input type="checkbox"/> Notice of Informal Patent Application (PTO-152)             |
| 3) <input checked="" type="checkbox"/> Information Disclosure Statement(s) (PTO-1449 or PTO/SB/08)<br>Paper No(s)/Mail Date <u>12/18/2005</u> . | 6) <input type="checkbox"/> Other: _____  |

## DETAILED ACTION

### *Claim Rejections - 35 USC § 102*

The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless –

(e) The invention was described in (1) an application for patent, published under section 122(b), by another filed in the United States before the invention by the applicant for patent or (2) a patent granted on an application for patent by another filed in the United States before the invention by the applicant for patent, except that an international application filed under the treaty defined in section 351(a) shall have the effects for purposes of this subsection of an application filed in the United States only if the international application designated the United States and was published under Article 21(2) of such treaty in the English language.

1. Claims 1, 4, 5, 8, 9, 12, 14, 17, 19, 22, 23, 26, 29 and 31 are rejected under 35 U.S.C. 102(e) over Samavedam (US Pub. No. 2004/0023478).

*As to claims 1, 5, 9, 14, 19 and 23, Samavedam discloses a method of manufacturing a semiconductor device (paragraph 0002) consisting of the steps:*

(a) Forming a masking pattern (paragraph 0023) on a laminate consisting of a first conductive layer (110) (Fig.1) and a second conductive layer (114) (paragraph 0025); (b) Forming a first pattern with a tapered sidewall (124, Fig. 4) portion by etching the laminate (paragraph 0031); and (c) Performing a plasma treatment to the first pattern with the tapered sidewall portion (paragraph 0030); and (d) Forming a second pattern by anisotropic etching the first pattern with the tapered sidewall portion (124) (paragraph 0031).

Samavedam discloses the use of metal film that includes, *titanium*, aluminum, zirconium, niobium tantalum and tungsten or an alloy containing any of these elements (paragraph 0022).

Samavedam discloses forming a mask pattern (paragraph 0023) on a laminate consisting of a first conductive layer (110) (Fig.3) and second conductive layer (114) on the first conductive layer (110), and a third conductive layer on the second conductive layer (paragraph 0042).

Samavedam discloses forming a mask pattern on a laminate consisting of a first conductive layer (110) (Fig.3) and a second conductive layer (114) over a semiconductor layer with a gate insulating film (108) interposed there between (paragraph 0030).

Samavedam discloses adding an impurity elements to the semiconductor layer as a shielding mask to form a region with the impurity elements in the semiconductor film wherein the region with the impurity elements overlaps with the first conductive layer (Fig.1, paragraph 0020).

*As to claim 4, 8, 12, 17, 22, 26, and 31*, Samavedam discloses that the first conductive layer is made of a metal nitride (paragraph 0030).

*As to claim 29*, Samavedam discloses that the lower first conductive layer is made of metal nitride (110, Fig.3) (paragraph 0030).

***Claim Rejections - 35 USC § 103***

The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negated by the manner in which the invention was made.

This application currently names joint inventors. In considering patentability of the claims under 35 U.S.C. 103(a), the examiner presumes that the subject matter of the various claims was commonly owned at the time any inventions covered therein were made absent any evidence to the contrary. Applicant is advised of the obligation under 37 CFR 1.56 to point out the inventor and invention dates of each claim that was not commonly owned at the time a later invention was made in order for the examiner to consider the applicability of 35 U.S.C. 103(c) and potential 35 U.S.C. 102(e), (f) or (g) prior art under 35 U.S.C. 103(a).

2. Claims 2, 3, 6, 7, 10, 11, 13, 15, 16, 18, 20, 21, 24, 25, 27, 28, 30 and 32 are rejected under 35 U.S.C. 103(a) over Samavedam (US Pub. No. 2004/0023478) as applied to claims 1, 5, 14, 19 and 23 in view of Hori (US Patent No. 5,445,710).

*As to claim 2, 6, 10, 15, 20 and 24, Samavedam discloses the plasma treatment using CF<sub>4</sub>/Ar or CF<sub>4</sub>/HBr or Cl<sub>2</sub> or He chemistry (paragraph 0030) but is silent about the use of pure argon for plasma treatment. However, Hori*

Art Unit: 1765

discloses the use of argon, hydrogen, or fluorocarbon (col.7, lines45-48) and oxygen (col.7, line 54) as an etching gas. Therefore, it would be obvious to one of ordinary skill in the art at the time of invention to use select argon as an etching gas as cited by the applicant in this claim because Hori suggests that the argon as an inert gas is a commonly used carrier gas in plasma deposition (col.7, lines 45-46) and in addition, use of etching gas depends on the material to be processed and etch selectivity desired in any given application (col.10, lines 1-6).

*As to claim 3, 7, 11, 16, 21 and 25*, Samavedam is silent about plasma treatment to remove polymer residue (paragraph 0030), a reaction product adhering to the tapered sidewall portion is removed by performing the plasma treatment step. However, Hori discloses the use of dry ashing to cause oxygen plasma to remove an organic resist (col.5, lines 13-16). Therefore, it would be obvious to one of ordinary skill in the art at the time of invention to include dry ashing process in the device fabrication discloses by Samavedam because Hori illustrates that dry ashing process allows the easy removal of resist which cannot be removed by wet etching method (col.5, lines18-21).

*As to claim 13, 18, 27 and 32*, Samavedam discloses the use of third conductive layer (paragraph 0042) but is silent about the material being used for this process. However, Samavedam discloses the use of high-melting point materials such as titanium nitride, iridium, tantalum, rhenium, molybdenum,

zirconium for the first and second metal layers (paragraph 0022 and claim 13). Therefore, it would be obvious to one of ordinary skill in the art at the time of invention to use high-melting point material for the third conductive layer because Samavedam teaches that the choice of material for the conductive layer depends on the work function of the metal being close to the valence band of silicon (i.e. a work function of about 5.1 eV) (paragraph 0022).

*As to claim 28 and 30*, Samavedam discloses a semiconductor device consisting of a gate electrode consisting of a lower first conductive layer and an upper second conductive layer (Fig.4, paragraph 0029) including titanium as its main component (paragraph 0022) and a third conductive layer on the second conductive layer (Fig.3, paragraph 0042).

Samavedam is silent about the width (thickness) of the first, second and third conductive layers (paragraph 0042). The width (thickness) of the conductive layer is dependent on several factors such as, the type of material, etch process and the doping level desired that could be a result-effective variable that can be optimized. See MPEP § 2144.05 II. Therefore, it would have been obvious to one of ordinary skill in the art at the time of invention to decide on the thickness of conductive layers so that the width of the first conductive layer is wider than the width of the second and third conductive layers. See MPEP § 2144.05 II.

Art Unit: 1765

**Conclusion**

The prior art made of record and not relied upon is considered pertinent to applicant's disclosure. Nagai (US Pub. No. 2004/0091820) discloses a method for removing a resist pattern and method for manufacturing semiconductor device.

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Maki A. Angadi whose telephone number is 571-272-8213. The examiner can normally be reached on 8 AM to 4.30 PM.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Nadine G. Norton can be reached on 571-272-1465. The fax phone number for the organization where this application or proceeding is assigned is 571-273-8300.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see <http://pair-direct.uspto.gov>. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

MA

NADINE NORTON  
ART UNIT 1765  
SUPERVISORY PATENT EXAMINER  
N N